TOSHIBA Field Effect Transistor with Built-in Schottky Barrier Diode Silicon N-Channel MOS Type (Ultra-High-Speed U-MOS Ⅲ)

# TPCA8A01-H

High Efficiency DC-DC Converter Applications

Notebook PC Applications

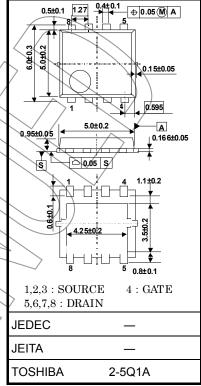
Portable Equipment Applications

- Built-in schottky barrier diode
   Low forward voltage: V<sub>DSF</sub> = -0.6 V (max)
- Small footprint due to a small and thin package
- · High speed switching
- Small gate charge: Q<sub>sw</sub> =11 nC (typ.)
- Low drain-source ON-resistance:  $R_{DS(ON)} = 4.3 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 70 \text{ S (typ.)}$
- Low leakage current: I<sub>DSS</sub> = 100 μA (max) (V<sub>DS</sub> = 30 V)
- Enhancement mode: V<sub>th</sub> = 1.1 to 2.3 V (V<sub>DS</sub> = 10 V, I<sub>D</sub> = 1 mA)

### Absolute Maximum Ratings (Ta = 25°C)

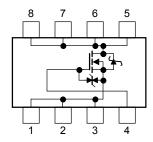
Characteristic		Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	30	V	
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		V <sub>DGR</sub>	30	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC (Note 1)	7	36	A	
	Pulsed (Note 1)	JDP	108	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Drain power dissipation (Tc=25°C)		PD	45	w	
Drain power dissipation (t = 10 s) (Note 2a)		PD	2.8	W	
Drain power dissipation (t = 10 s) (Note 2b)		PD	1.6	W	
Single-pulse avalanche energy (Note 3)		EAS	168	mJ	
Avalanche current \		IAR	36	Α	
Repetitive avalanche energy (Tc=25°C) (Note 4)		EAR	2.1	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	

Unit: mm



Weight: 0.080 g (typ.)

#### **Circuit Configuration**



Note: For Notes 1 to 4, refer to the next page.

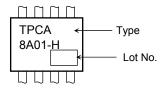
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care. Schottky barrier diodes have large-reverse-current-leakage characteristic compared to other rectifier products. This current leakage combined with improper operating temperature or voltage may cause thermal runaway. Please take forward and reverse loss into consideration during design.

#### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc=25°C)	R <sub>th (ch-c)</sub>	2.78	°C/W
Thermal resistance, channel to ambient $(t=10\;s) \eqno(Note\;2a)$	R <sub>th (ch-a)</sub>	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	78.1	°C/W

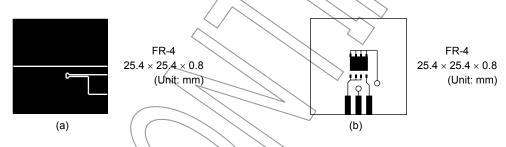
### Marking (Note 5)



Note 1: The channel temperature should not exceed 150°C during use

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)



Note 3:  $V_{DD} = 24 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial), L = 0.1 mH,  $R_G = 25 \Omega$ ,  $I_{AR} = 36 \text{ A}$ 

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: \* Weekly code: (Three digits)

Week of manufacture

(01 for first week of year, continuing up to 52 or 53)

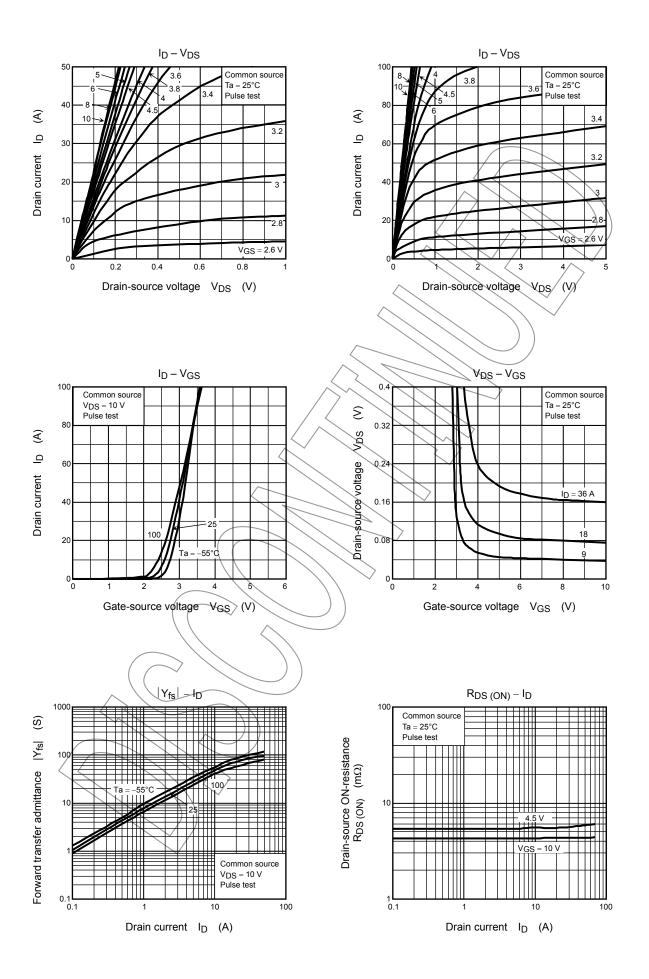
Year of manufacture (The last digit of the calendar year)

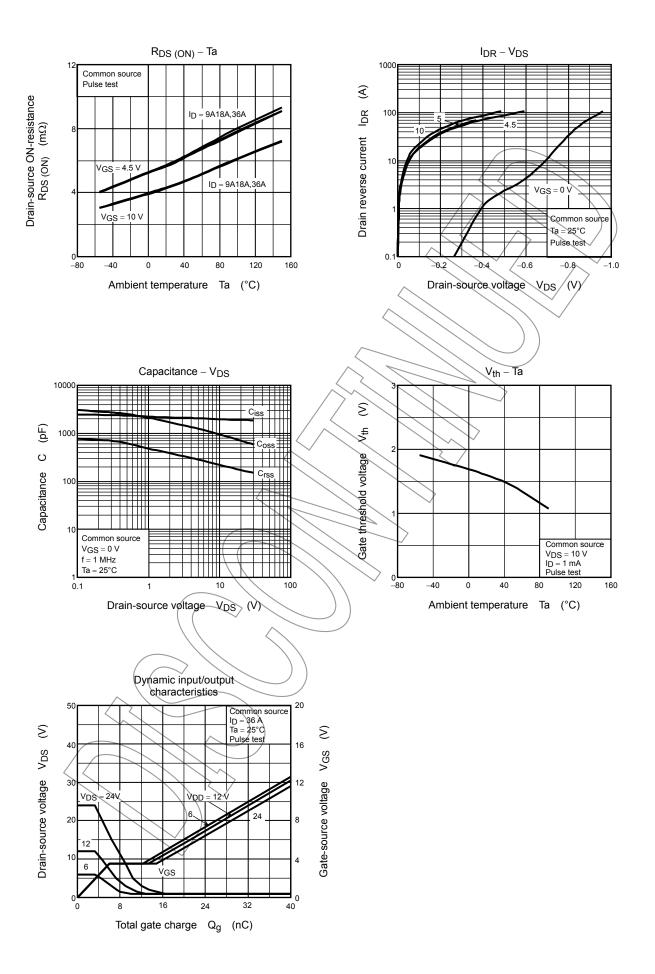
## **Electrical Characteristics (Ta = 25°C)**

Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μΑ
Drain cut-off curr	ent	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	_	_	100	μА
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_		V
		V <sub>(BR)DSX</sub>	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15			v
Gate threshold vo	oltage	$V_{th}$	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	1.1	1	2.3	V
Drain-source ON-resistance		Б	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 18 A	y	6.2	8.5	- mΩ
		R <sub>DS</sub> (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 18 A	/	4.3	5.6	
Forward transfer	admittance	Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, I_D = 18 \text{ A}$	35	70	(+)	S
Input capacitance	9	C <sub>iss</sub>		/	1970	\ }	
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	1	240/	>	pF
Output capacitance		Coss			950 /	_	
Switching time	Rise time	t <sub>r</sub>	10 V □ ID= 18A	1	æ		
	Turn-on time	t <sub>on</sub>	VGS OV COUT		18		ns
	Fall time	t <sub>f</sub>	R = 0.00 M	>-	10	_	115
	Turn-off time	t <sub>off</sub>	V <sub>DD</sub> ≈ 15 V Duty ≤ 1%, t <sub>W</sub> = 10 μs	_	44	_	
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 36 \text{ A}$		35		-
			$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 36 \text{ A}$	_	19	_	
Gate-source cha	rge 1	Q <sub>gs1</sub>			6	_	nC
Gate-drain ("Miller") charge		Qgd	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 36 \text{ A}$		8.8		
Gate switch charge		Qsw			11		

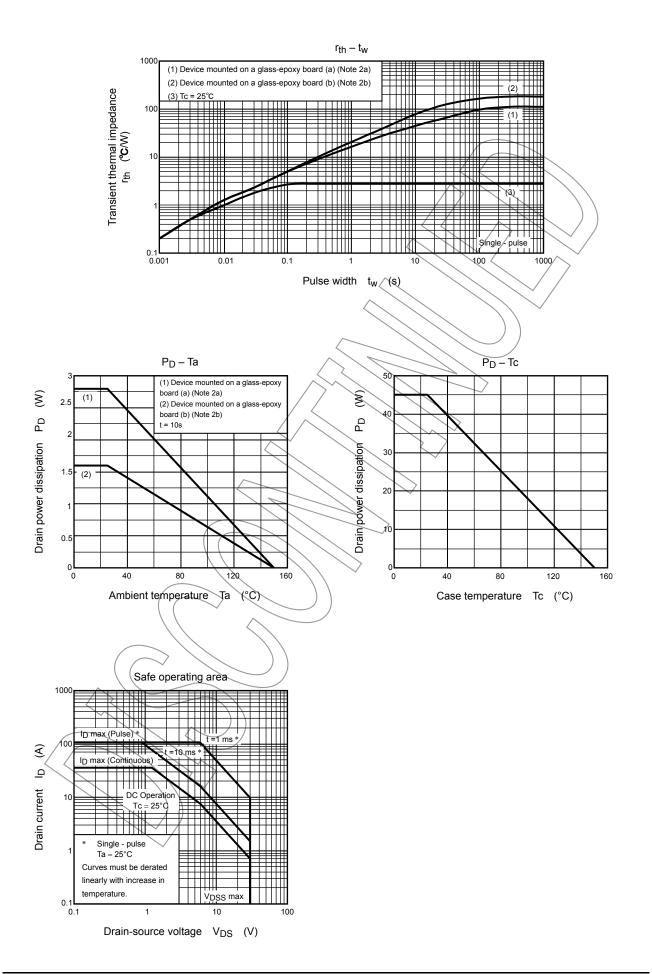
# Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Peak forward current Pulse (Note 1)	IDRP	_	_	_	108	Α
Forward voltage (diode)	Vaar	$I_{DR} = 1.0 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.45	- 0.6	V
Torward voltage (diode)	VDSF	$I_{DR} = 36 \text{ A}, V_{GS} = 0 \text{ V}$			- 1.2	V

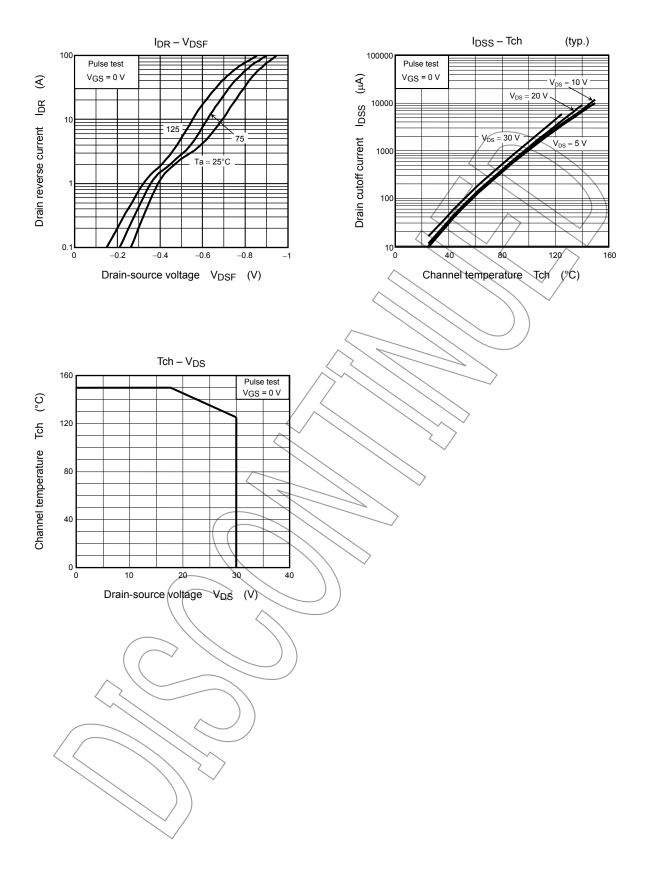




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